Is Now Part of

ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

FAIRCHILD SEMICONDUCTOR TM

June 2001

FDFS2P106A

Integrated 60V P-Channel PowerTrench® MOSFET and Schottky Diode

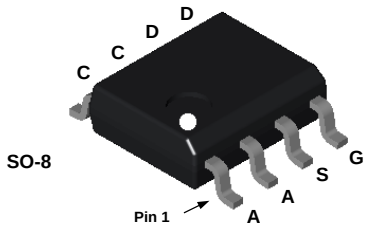
General Description

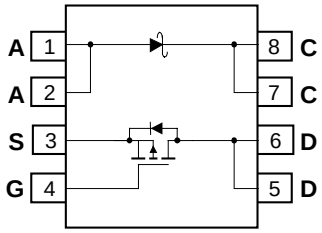
The FDFS2P106A combines the exceptional performance of Fairchild's PowerTrench MOSFET technology with a very low forward voltage drop Schottky barrier rectifier in an SO-8 package.

This device is designed specifically as a single package solution for DC to DC converters. It features a fast switching, low gate charge MOSFET with very low on-state resistance. The independently connected Schottky diode allows its use in a variety of DC/DC converter topologies.

Features

- –3.0 A, –60V $R_{DS(ON)}$ = 110 mΩ @ V_{GS} = –10 V
  $R_{DS(ON)}$ = 140 mΩ @ V_{GS} = –4.5 V
- V_F < 0.45 V @ 1 A (T_J = 125°C)
  V_F < 0.53 V @ 1 A
  V_F < 0.62 V @ 2 A
- Schottky and MOSFET incorporated into single power surface mount SO-8 package
- Electrically independent Schottky and MOSFET pinout for design flexibility





Absolute Maximum Ratings

T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	MOSFET Drain-Source Voltage		–60	V
V_{GSS}	MOSFET Gate-Source Voltage		±20	V
I_D	Drain Current – Continuous	(Note 1a)	–3	A
	– Pulsed		–10	
P_D	Power Dissipation for Dual Operation		2	W
	Power Dissipation for Single Operation	(Note 1a)	1.6	
		(Note 1b)	1	
		(Note 1c)	0.9	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		–55 to +150	°C
V_{RRM}	Schottky Repetitive Peak Reverse Voltage		45	V
I_O	Schottky Average Forward Current	(Note 1a)	1	A

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDFS2P106A	FDFS2P106A	13''	12mm	2500 units

Electrical Characteristics

T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	V_{GS} = 0 V, I_D = –250 µA	–60			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = –250 µA, Referenced to 25°C		–60		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = –48 V, V_{GS} = 0 V			–1	µA
I_{GSSF}	Gate–Body Leakage, Forward	V_{GS} = 20V, V_{DS} = 0 V			100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	V_{GS} = –20 V V_{DS} = 0 V			–100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = –250 µA	–1	–1.6	–3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = –250 µA,Referenced to 25°C		4		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	V_{GS} = –10 V, I_D = –3A V_{GS} = –4.5 V, I_D = –2.7 A V_{GS} = –10 V, I_D = –3 A, T_J=125°C		91 112 150	110 140 192	mΩ
$I_{D(on)}$	On–State Drain Current	V_{GS} = –10 V, V_{DS} = –5 V	–10			A
g_{FS}	Forward Transconductance	V_{DS} = –5 V, I_D = –3.3 A		8		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = –30 V, V_{GS} = 0 V, f = 1.0 MHz		714		pF
C_{oss}	Output Capacitance			84		pF
C_{rss}	Reverse Transfer Capacitance			33		pF
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = –30 V, I_D = –1 A, V_{GS} = –10 V, R_{GEN} = 6 Ω		8	15	ns
t_r	Turn–On Rise Time			11	19	ns
$t_{d(off)}$	Turn–Off Delay Time			28	45	ns
t_f	Turn–Off Fall Time			8.5	17	ns
Q_g	Total Gate Charge	V_{DS} = –30V, I_D = –3A, V_{GS} = –10 V		15	21	nC
Q_{gs}	Gate–Source Charge			2		nC
Q_{gd}	Gate–Drain Charge			3		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain–Source Diode Forward Current				–1.3	A
V_{SD}	Drain–Source Diode Forward Voltage	V_{GS} = 0 V, I_S = –1.3 A (Note 2)		–0.8	–1.2	V

Electrical Characteristics (continued)

T_A = 25°C unless otherwise noted

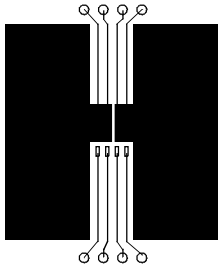
Symbol	Parameter	Test Conditions		Min	Typ	Max	Units
Schottky Diode Characteristics							
I_R	Reverse Leakage	V_R = 45 V	T_J = 25°C		2.8	80	µA
			T_J = 125°C		2.2	80	mA
V_F	Forward Voltage	I_F = 1 A	T_J = 25°C		0.44	0.53	V
			T_J = 125°C		0.34	0.45	
		I_F = 2 A	T_J = 25°C		0.49	0.62	
			T_J = 125°C		0.42	0.57	

Thermal Characteristics

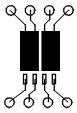
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

Notes:

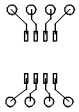
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 78°C/W when mounted on a 0.5in^2 pad of 2 oz copper



b) 125°C/W when mounted on a 0.02 in^2 pad of 2 oz copper



c) 135°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

Typical Characteristics

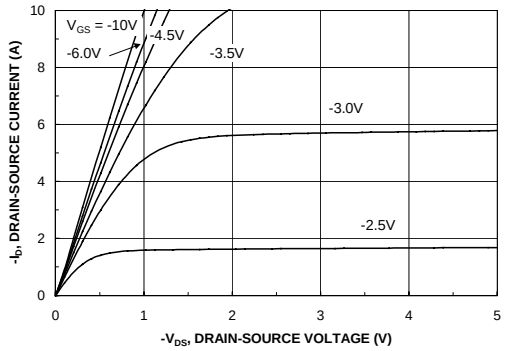


Figure 1. On-Region Characteristics.

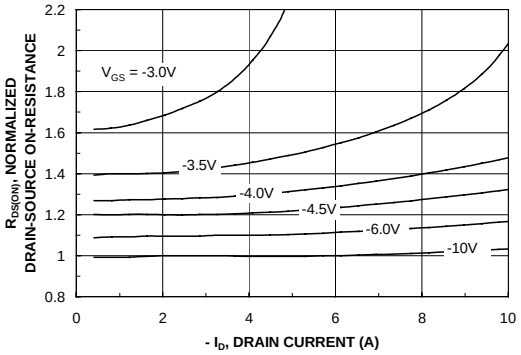


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

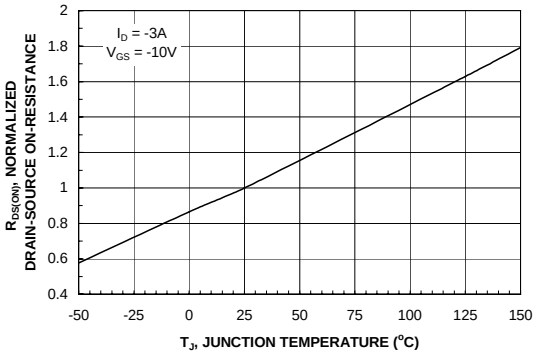


Figure 3. On-Resistance Variation with Temperature.

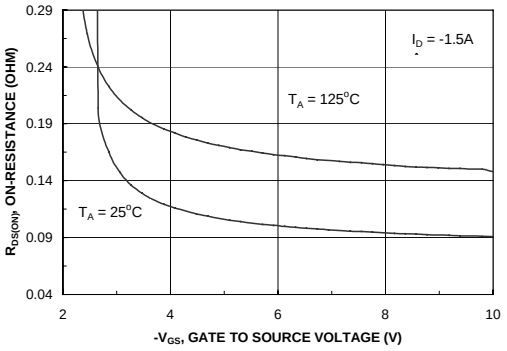


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

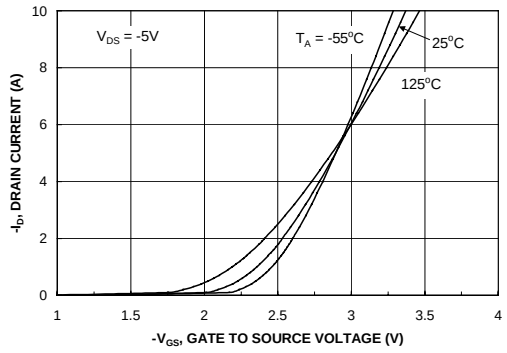


Figure 5. Transfer Characteristics.

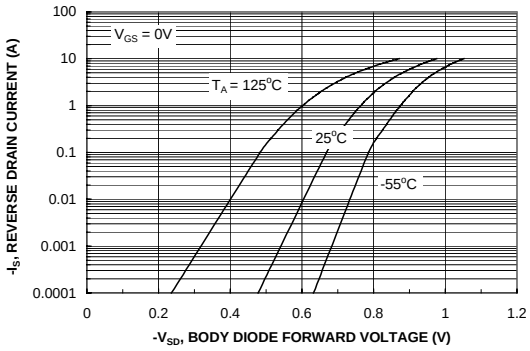


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

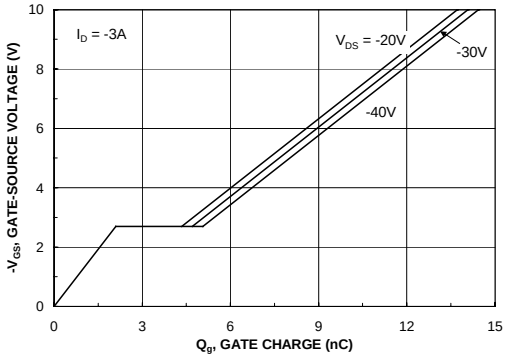


Figure 7. Gate Charge Characteristics.

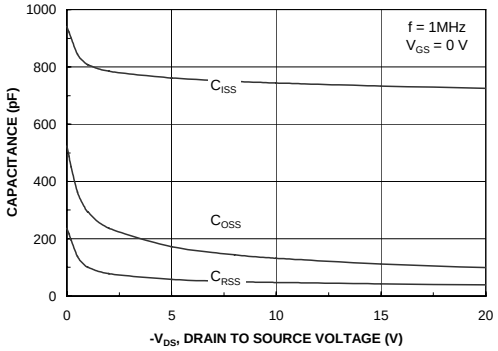


Figure 8. Capacitance Characteristics.

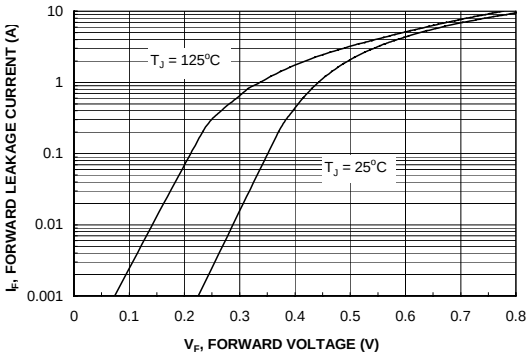


Figure 9. Schottky Diode Forward Voltage.

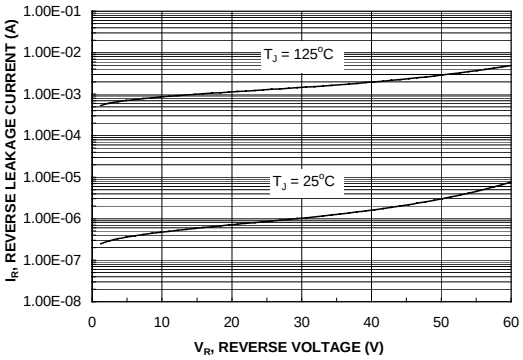


Figure 10. Schottky Diode Reverse Current.

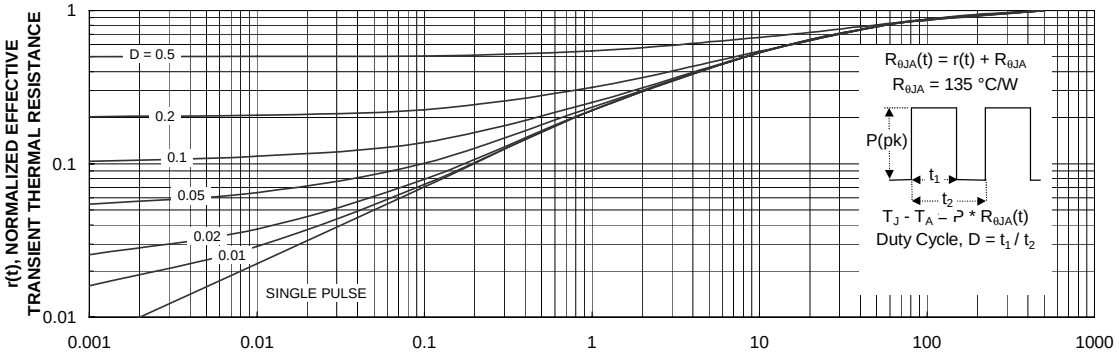


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FAST ®	OPTOPLANAR™	STAR*POWER™
Bottomless™	FASTr™	PACMAN™	Stealth™
CoolFET™	FRFET™	POP™	SuperSOT™-3
CROSSVOLT™	GlobalOptoisolator™	Power247™	SuperSOT™-6
DenseTrench™	GTO™	PowerTrench®	SuperSOT™-8
DOME™	HiSeC™	QFET™	SyncFET™
EcoSPARK™	ISOPLANAR™	QS™	TinyLogic™
E^2CMOS^{TM}	LittleFET™	QT Optoelectronics™	TruTranslation™
EnSigna™	MicroFET™	Quiet Series™	UHC™
FACT™	MICROWIRE™	SILENT SWITCHER®	UltraFET ®
FACT Quiet Series™	OPTOLOGIC™	SMART START™	VCX™

STAR*POWER is used under license

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.
As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative